



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	2.0Ω @ Vgs = 10V	300mA
007	3.0Ω @ Vgs = 4.5V	245mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions
- Backlighting

Features and Benefits

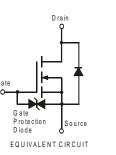
- Low On-Resistance: RDS(ON)
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An automotive-compliant part is available under separate datasheet (DMN601WKQ)

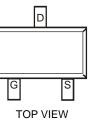
Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)









Pin Out Configuration

Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nulliber	Fackage	Qty.	Carrier	
DMN601WK-7	SOT323	3000	Tape & Reel	

SOT323

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

Date Code Key			ĸ	лк Ş		YM = Da Y or $\overline{Y} =$	roduct Typ ate Code N Year (ex: hth (ex: 4 =	L = 2024)	Code			
Year	2012	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	Z	-	L	М	N	Р	R	S	Т	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Cha	aracteristic	Symbol	Value	Units
Drain-Source Voltage		Vdss	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 5)	Continuous Pulsed (Note 6)	lD	300 800	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient	R _θ JA	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	Vgs = 0, Id = 10µA
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μA	VDS = 60V, VGS = 0
Gate-Source Leakage	Igss	_		±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(th)	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Statia Drain Course On Desistance		_	1.4	2.0	Ω	Vgs = 10V, Id = 0.5A
Static Drain-Source On-Resistance	RDS(ON)		1.5	3.0		VGS = 4.5V, ID = 0.2A
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	_	50	pF	
Output Capacitance	Coss	_	_	25	pF	V _{DS} = 25V, V _{GS} = 0, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	_	5.0	pF	

5. Device mounted on FR-4 PCB.

Notes:

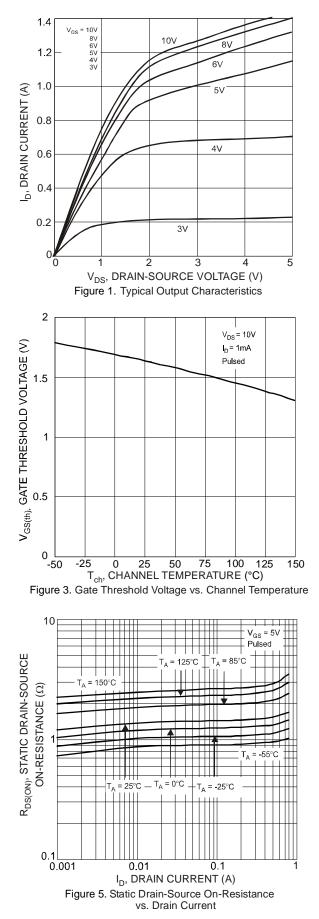
6. Pulse width \leq 10µs, Duty Cycle \leq 1%.

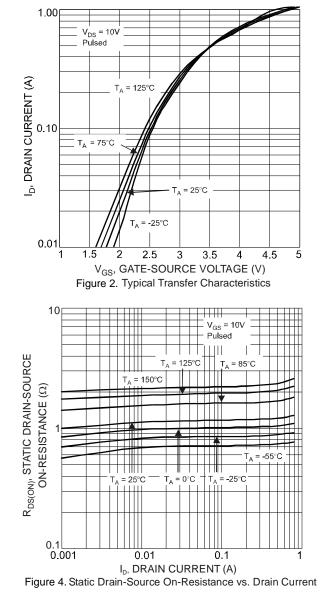
7. Short duration pulse test used to minimize self-heating effect.

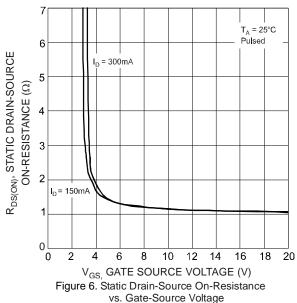
8. Guaranteed by design. Not subject to production testing.





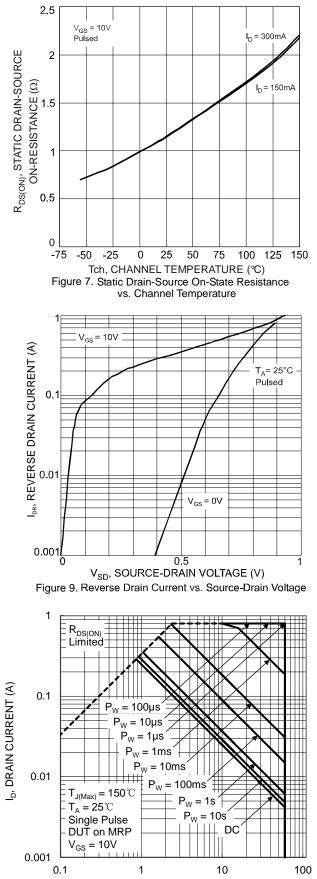


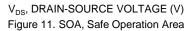












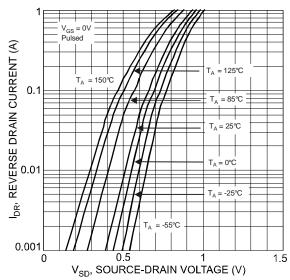
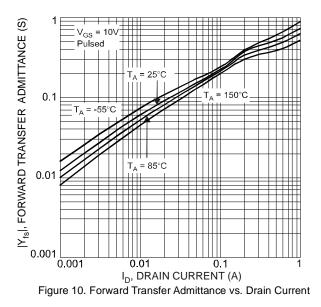


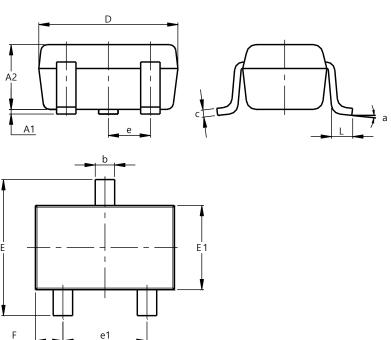
Figure 8. Reverse Drain Current vs. Source-Drain Voltage





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

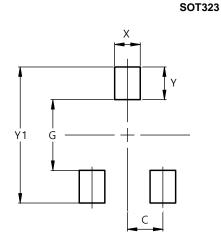


SOT323

SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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